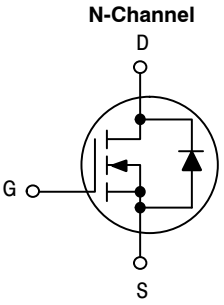
MOSFET – N-Channel, SOT-23

2.8 A, 20 V

MGSF2N02EL, MVSF2N02EL

2.8 A, 20 V
$R_{DS(on)}$ = 85 mΩ (max)



These miniature surface mount MOSFETs low $R_{DS(on)}$ assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry.

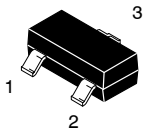
Features

- Low $R_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- I_{DSS} Specified at Elevated Temperature
- AEC Q101 Qualified and PPAP Capable – MVSF2N02EL
- These Devices are Pb-Free and are RoHS Compliant

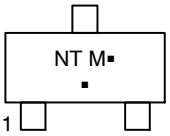
Applications

- DC-DC Converters
- Power Management in Portable and Battery Powered Products, ie: Computers, Printers, PCMCIA Cards, Cellular and Cordless Telephones

MARKING DIAGRAM

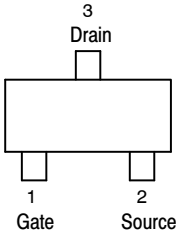


SOT-23
CASE 318
STYLE 21



xxx = Specific Device Code
M = Date Code
▪ = Pb-Free Package

PIN ASSIGNMENT



MAXIMUM RATINGS (T_J = 25 °C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	20	Vdc
Gate-to-Source Voltage – Continuous	V_{GS}	± 8.0	Vdc
Drain Current – Continuous @ T_A = 25 °C – Single Pulse (t_p = 10 μs)	 I_D I_{DM}	 2.8 5.0	A
Total Power Dissipation @ T_A = 25°C	P_D	1.25	W
Operating and Storage Temperature Range	T_J, T_{stg}	– 55 to 150	°C
Thermal Resistance Junction-to-Ambient (Note 1) Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100 300	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 10 seconds	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. 1” Pad, t < 10 sec.
2. Min pad, steady state.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (Note 3) (V_{GS} = 0 Vdc, I_D = 10 μAdc) Temperature Coefficient (Positive)		$V_{(BR)DSS}$	20 –	– 22	– –	Vdc mV/°C
Zero Gate Voltage Drain Current (V_{DS} = 20 Vdc, V_{GS} = 0 Vdc) (V_{DS} = 20 Vdc, V_{GS} = 0 Vdc, T_J = 125 °C)		I_{DSS}	– –	– –	1.0 10	μAdc
Gate-Source Leakage Current (V_{GS} = ± 8.0 Vdc, V_{DS} = 0 Vdc)		I_{GSS}	–	–	±100	nA
ON CHARACTERISTICS (Note 3)						
Gate-Source Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μAdc) Threshold Temperature Coefficient (Negative)		$V_{GS(th)}$	0.5 –	– –2.3	1.0 –	Vdc mV/°C
Static Drain-to-Source On-Resistance (V_{GS} = 4.5 Vdc, I_D = 3.6 A) (V_{GS} = 2.5 Vdc, I_D = 3.1 A)		$R_{DS(on)}$	– –	78 105	85 115	mΩ
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 5.0 Vdc, V_{GS} = 0 V, f = 1.0 MHz)	C_{iss}	–	150	–	pF
Output Capacitance		C_{oss}	–	130	–	
Transfer Capacitance		C_{rss}	–	45	–	
SWITCHING CHARACTERISTICS (Note 4)						
Turn-On Delay Time	(V_{DD} = 16 Vdc, I_D = 2.8 Adc, V_{gs} = 4.5 V, R_G = 2.3 Ω)	$t_{d(on)}$	–	6.0	–	ns
Rise Time		t_r	–	95	–	
Turn-Off Delay Time		$t_{d(off)}$	–	28	–	
Fall Time		t_f	–	125	–	
Gate Charge	(V_{DS} = 16 Vdc, I_D = 1.75 Adc, V_{GS} = 4.0 Vdc) (Note 3)	Q_T	–	3.5	–	nC
		Q_{gs}	–	0.6	–	
		Q_{gd}	–	1.5	–	
SOURCE–DRAIN DIODE CHARACTERISTICS						
Forward Voltage	(I_S = 1.0 Adc, V_{GS} = 0 Vdc) (Note 3)	V_{SD}	– –	0.76 –	1.2 –	V
Reverse Recovery Time	(I_S = 1.0 Adc, V_{GS} = 0 Vdc, dI_S/dt = 100 A/μs) (Note 3)	t_{rr}	–	104	–	ns
		t_a	–	42	–	
		t_b	–	62	–	
Reverse Recovery Stored Charge		Q_{RR}	–	0.20	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperature.

ORDERING INFORMATION

Device	Package	Shipping†
MGSF2N02ELT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MVSF2N02ELT1G*		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*MVSF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

TYPICAL CHARACTERISTICS

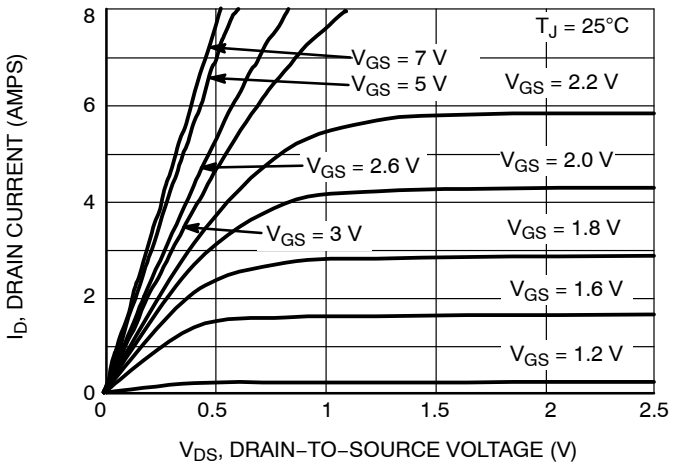


Figure 1. On-Region Characteristics

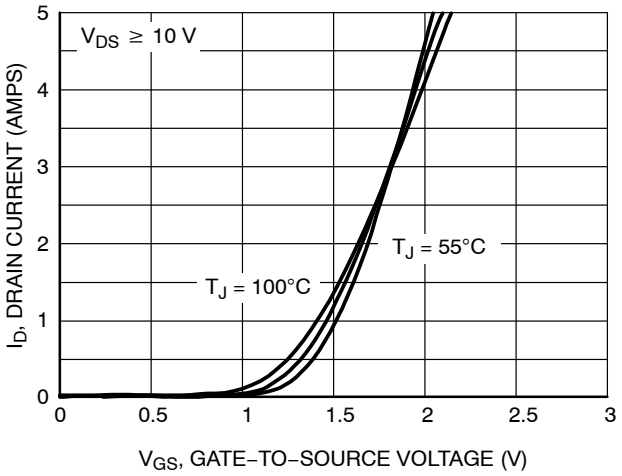


Figure 2. Transfer Characteristics

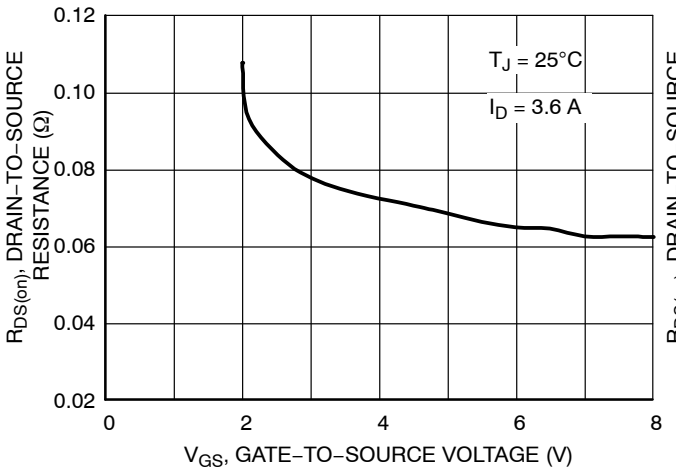


Figure 3. On-Resistance vs. Gate-to-Source Voltage

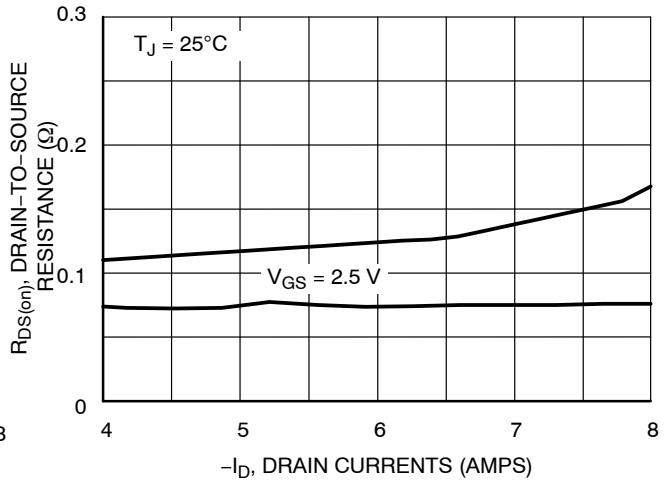


Figure 4. On-Resistance vs. Gate Voltage

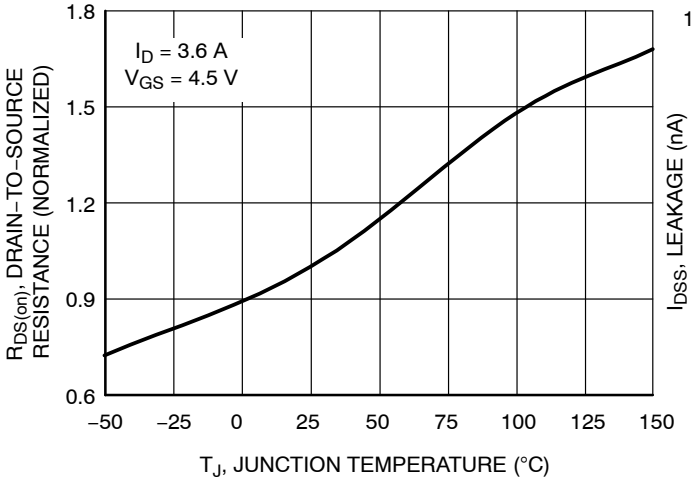


Figure 5. On-Resistance Variation with Temperature

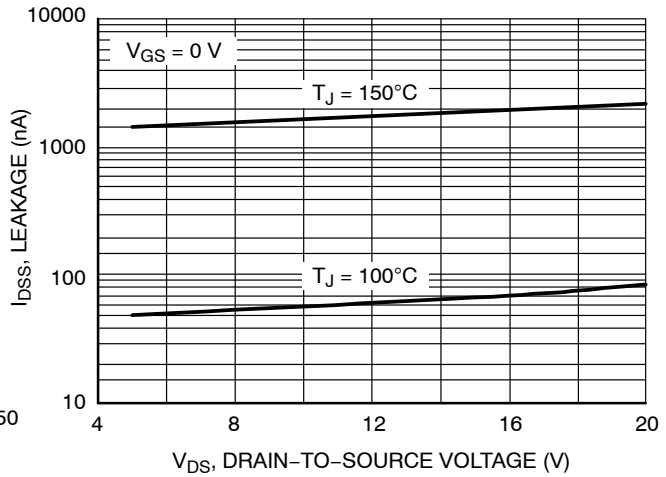


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

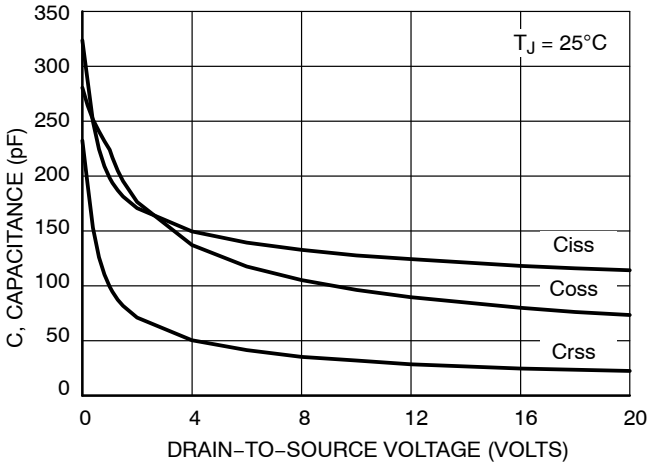


Figure 7. Capacitance Variation

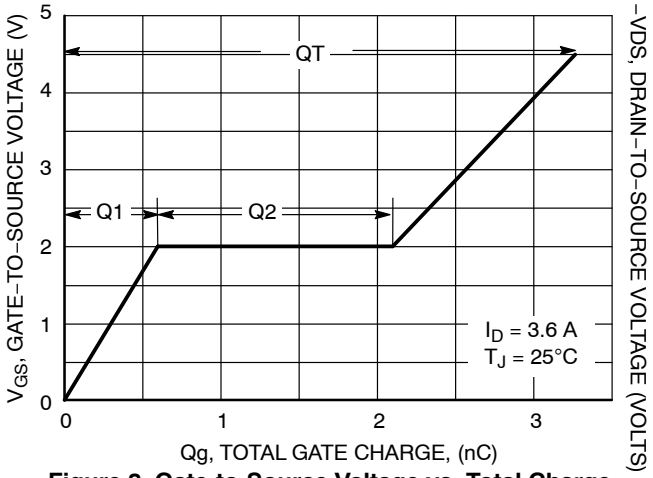


Figure 8. Gate-to-Source Voltage vs. Total Charge

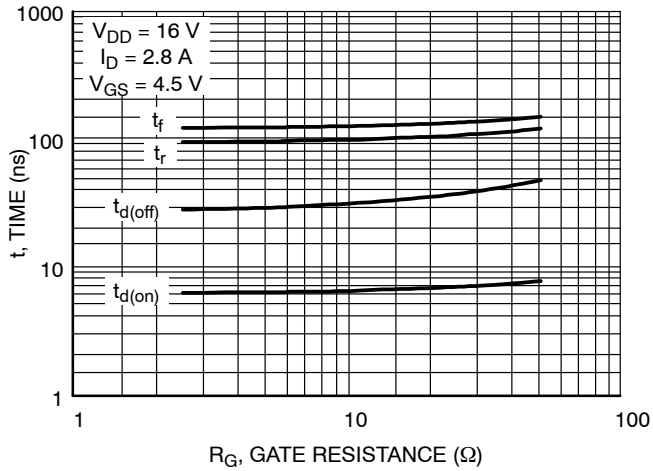


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

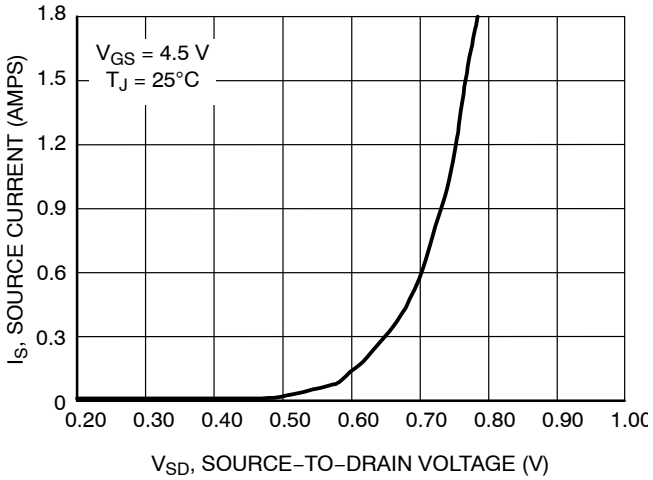
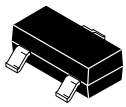


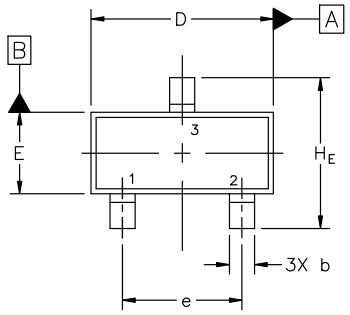
Figure 10. Diode Forward Voltage vs. Current



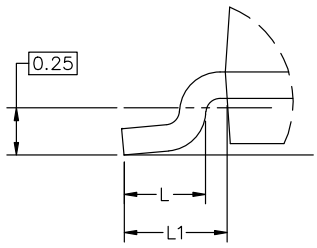
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

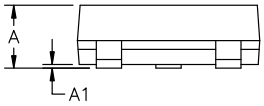
DATE 14 AUG 2024



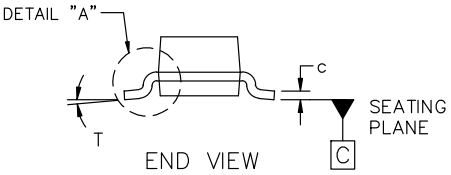
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

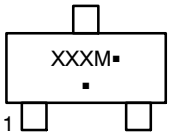


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

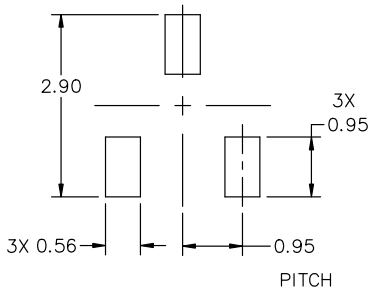
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**		**PAGE 1 OF 2**

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

ADDITIONAL INFORMATION

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